

N-channel TrenchMOS standard level FET Rev. 02 — 17 December 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC converters

Switched-mode power supplies

1.4 Quick reference data

Table 1.	ble 1. Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-	-	18	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	-	79	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 9 A; T _j = 25 °C	-	80	90	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 18 A; V _{DS} = 80 V; T _j = 25 °C	-	8	-	nC

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2. Pinning information

Table 2.	Pinning information			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHB18NQ10T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C	-	13	А
		V _{GS} = 10 V; T _{mb} = 25 °C	-	18	А
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	72	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	79	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	18	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	72	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 11 \text{ A}; \\ V_{\text{sup}} \leq 25 \text{ V}; \text{ unclamped}; \text{t}_{\text{p}} = 100 \mu\text{s}; \\ R_{\text{GS}} = 50 \Omega $	-	70	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ R _{GS} = 50 Ω ; unclamped	-	18	А

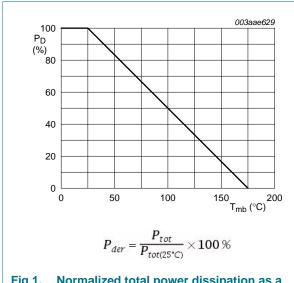
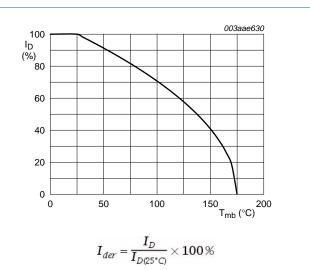


Fig 1. Normalized total power dissipation as a function of mounting base temperature

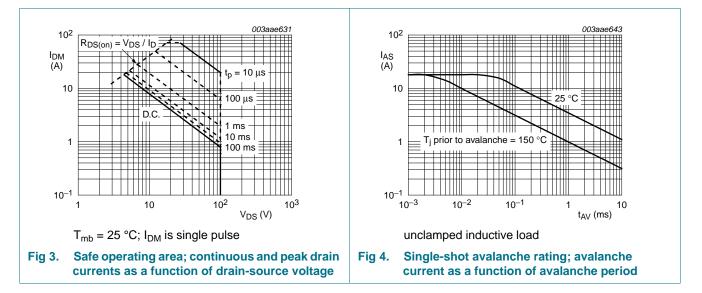




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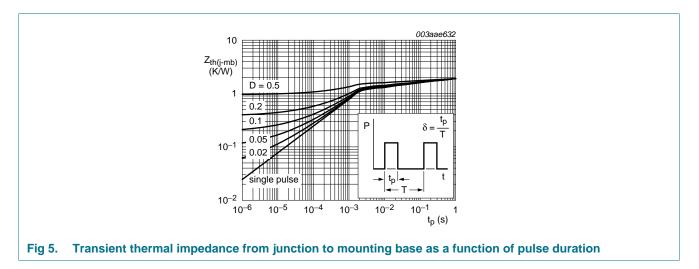
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	1.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W



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6. Characteristics

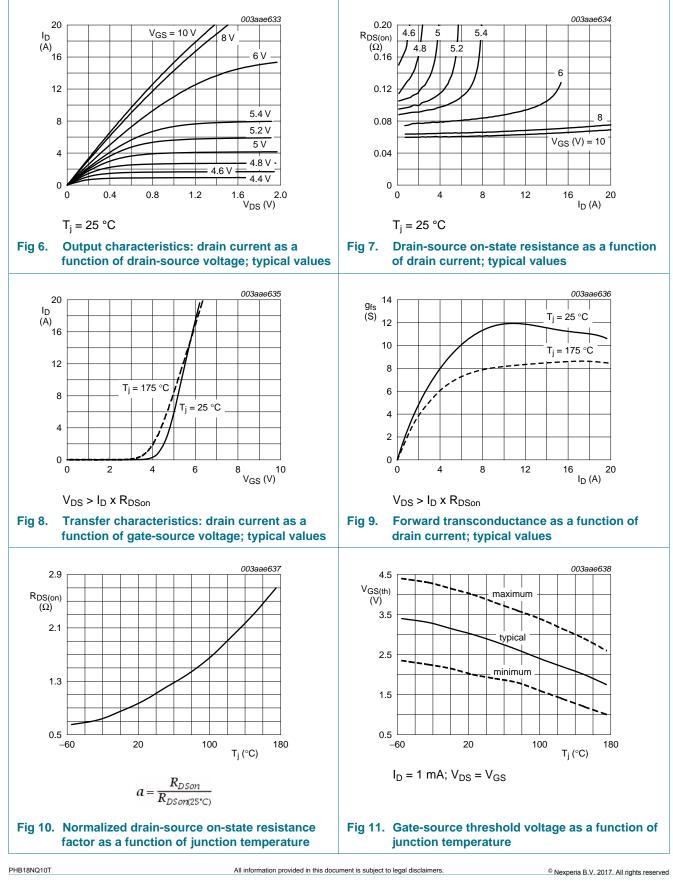
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
(01()000	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 9 A; T _j = 175 °C	-	-	243	mΩ
	resistance	V _{GS} = 10 V; I _D = 9 A; T _j = 25 °C	-	80	90	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 18 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	21	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \ ^{\circ}C$	-	4	-	nC
Q _{GD}	gate-drain charge		-	8	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	633	-	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	103	-	pF
C _{rss}	reverse transfer capacitance		-	61	-	pF
d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 2.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	6	-	ns
tr	rise time	R _{G(ext)} = 5.6 Ω; T _j = 25 °C	-	36	-	ns
d(off)	turn-off delay time		-	18	-	ns
t _f	fall time		-	12	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
-s	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 18 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.92	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 18 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	55	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	135	-	nC

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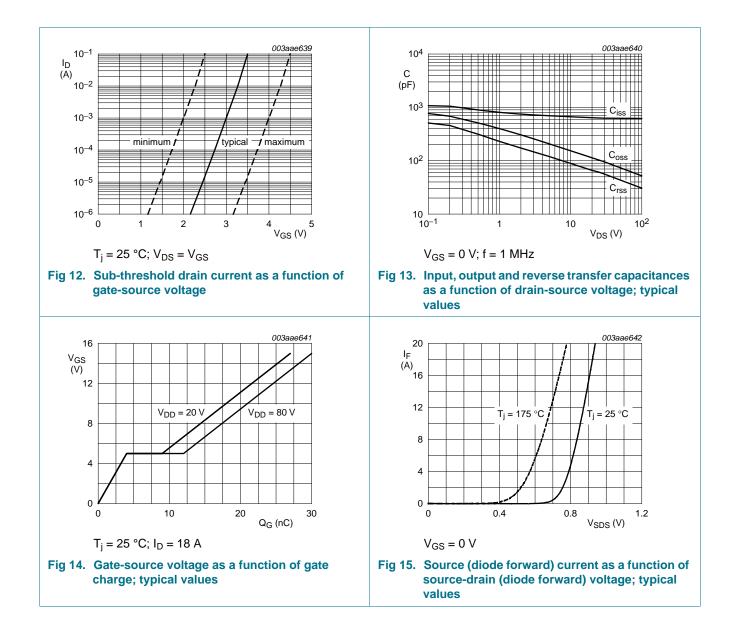
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7. Package outline

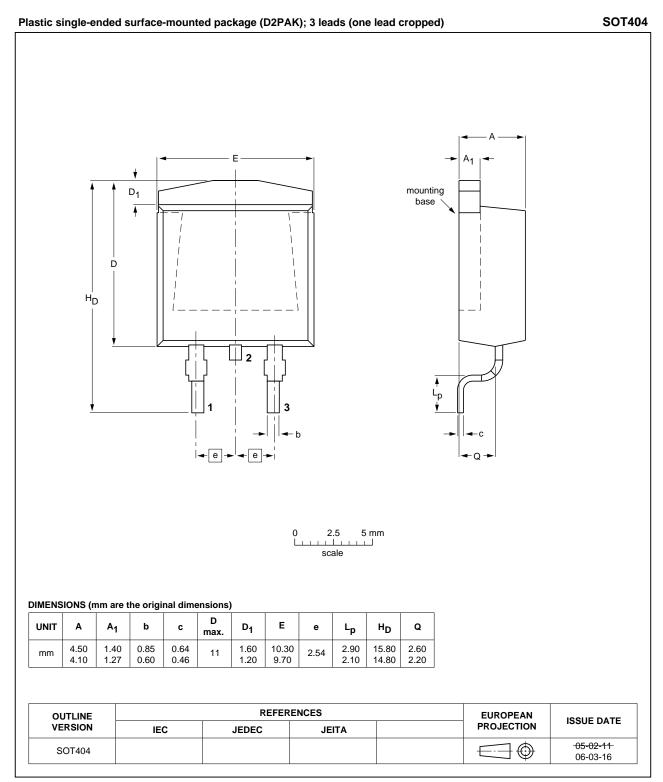


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.	Revision history					
Document	: ID	Release date	Data sheet status	Change notice	Supersedes	
PHB18NQ	10T v.2	20101217	Product data sheet	-	PHB_PHD_PHP18NQ10T v.1	
Modifications:		 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
		 Legal texts 	have been adapted to the	e new company na	me where appropriate.	
		 Type number 	er PHB18NQ10T separate	ed from data sheet	PHB_PHD_PHP18NQ10T v.1.	
PHB_PHD	_PHP18NQ10T v.1	19990801	Product specification	-	-	

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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